

# Challenge 2

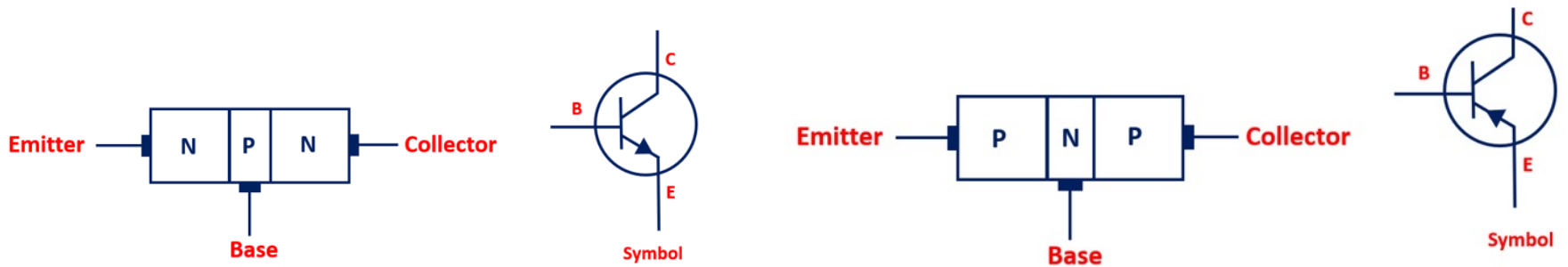
## CS-EEE

Introduction to  
Transistors

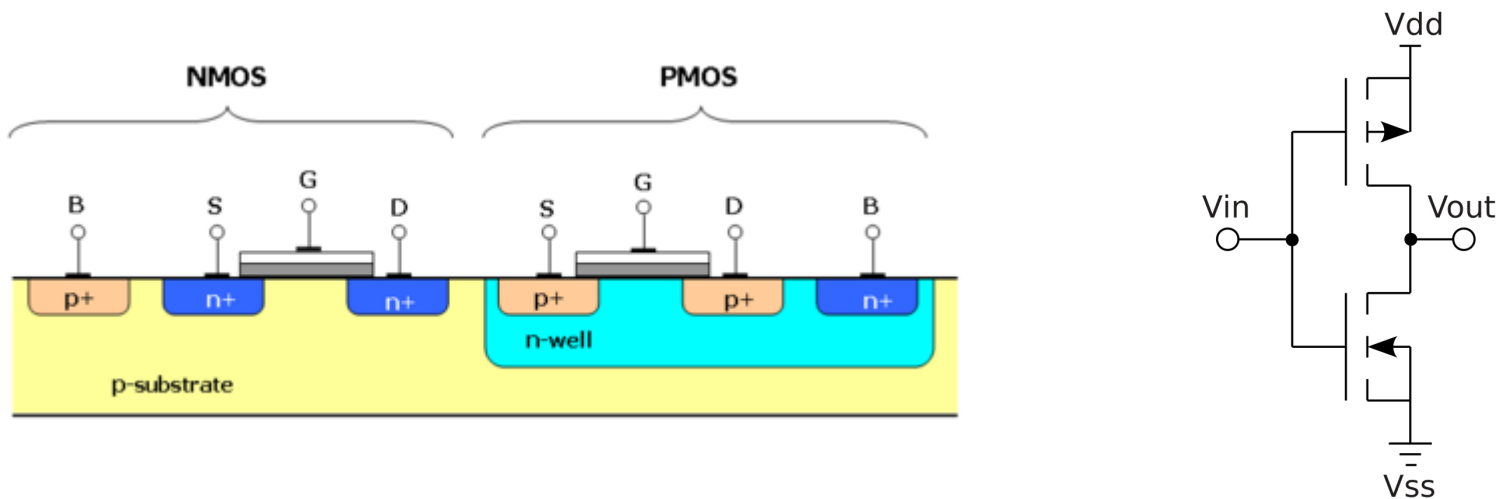


# Transistor Types

## Bipolar Junction Transistor



## Complementary metal–oxide–semiconductor (CMOS)

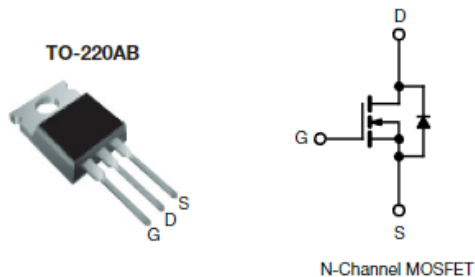


# Transistor Types

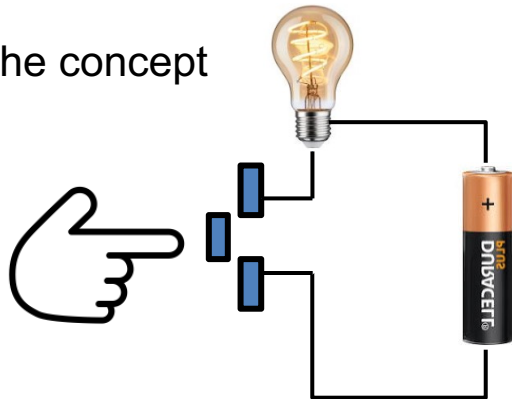
Characteristic	MOSFET	BJT (NPN/PNP)
Transistor Types	N-Channel (e.g., IRF520, IRF740), P-Channel (e.g., IRF9530, IRF9630)	NPN (e.g., 2N3904, BC547), PNP (e.g., 2N3906, BC557)
Input Control	Voltage-controlled device	Current-controlled device
Input Impedance	Extremely high	Moderate to low
Switching Speed	Very fast (e.g., nanoseconds to microseconds)	Fast to moderate (e.g., microseconds to milliseconds)
Voltage Rating	low to high voltage	low to moderate voltage
Current Rating	low to high current	low to moderate current
Applications	Digital and analog applications	Amplification, switching, signal processing

# How do they work? At entry level

## ➤ Symbol of MOSFET

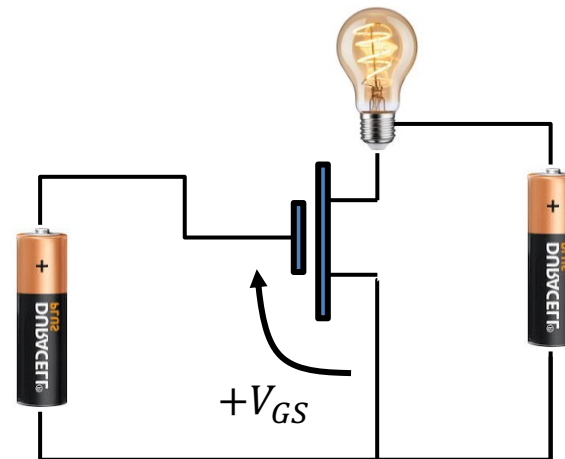


## ➤ The concept



- Functions as a switch with a control terminal

## ➤ The circuit implementation



- A positive  $V_{GS}$
- Drain (D) and Source (S) are connected like a switch!
- The  $V_{GS}$  must be large enough to turn on the switch, hence larger than a  $V_{TH}$
- Control the gate voltage to control the current flows through the light bulb

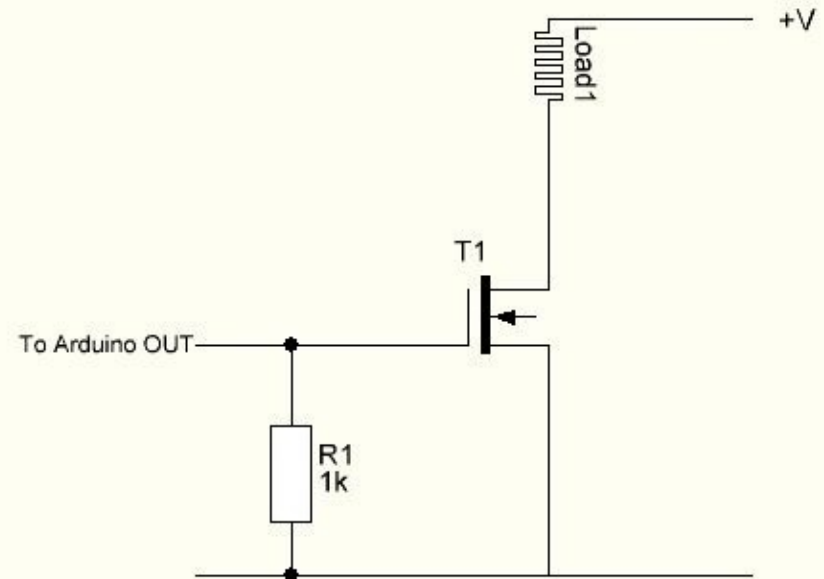
# How to use it?

- The transistor in serial with the load
- The gate of the transistor is connected to the selected IO pins from Arduino.
- R1 is called a pull-down resistor
- When the IO pin is high, 5V is connected to the transistor, and turn it on
- Current flows from supply +V to the Load.

If  $+V = 5V$ , can we use IO pin to connect to the load?

Can we connect the load on the other side of the transistor?

## Circuit schematics

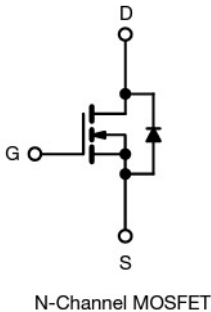
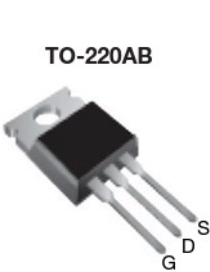




www.vishay.com

IRF520

Vishay Siliconix



PRODUCT SUMMARY		
$V_{DS}$ (V)	100	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.27
$Q_g$ max. (nC)	16	
$Q_{gs}$ (nC)	4.4	
$Q_{gd}$ (nC)	7.7	
Configuration	Single	

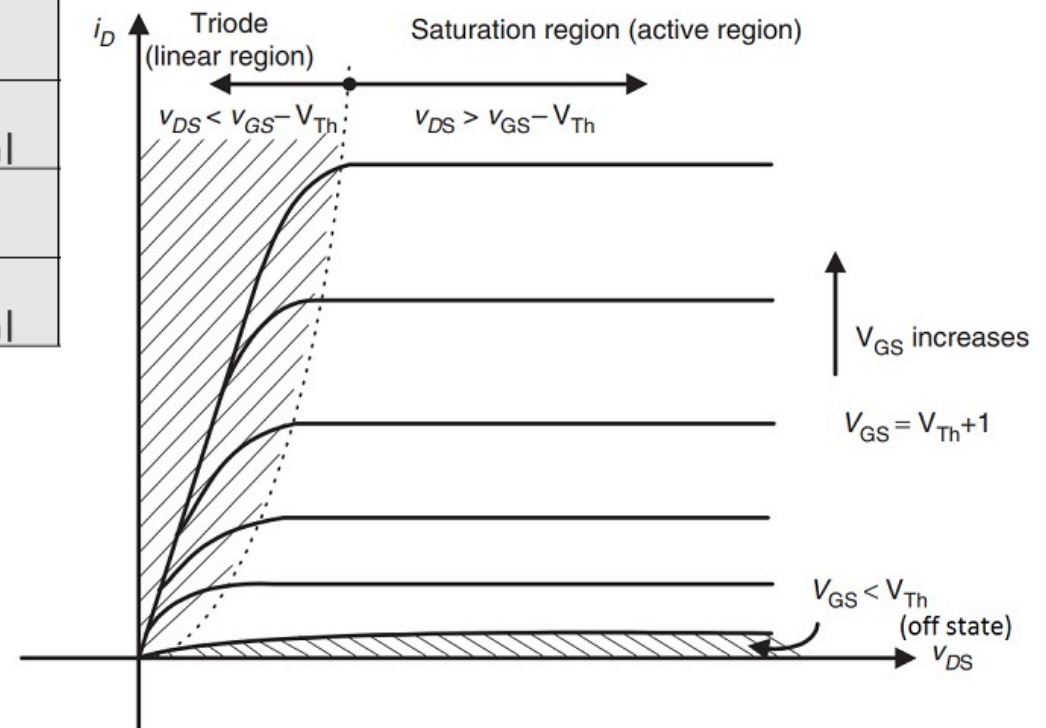
ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V <sub>DS</sub>	100	V
Gate-source voltage			V <sub>GS</sub>	± 20	
Continuous drain current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	9.2	A
		T <sub>C</sub> = 100 °C		6.5	

Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
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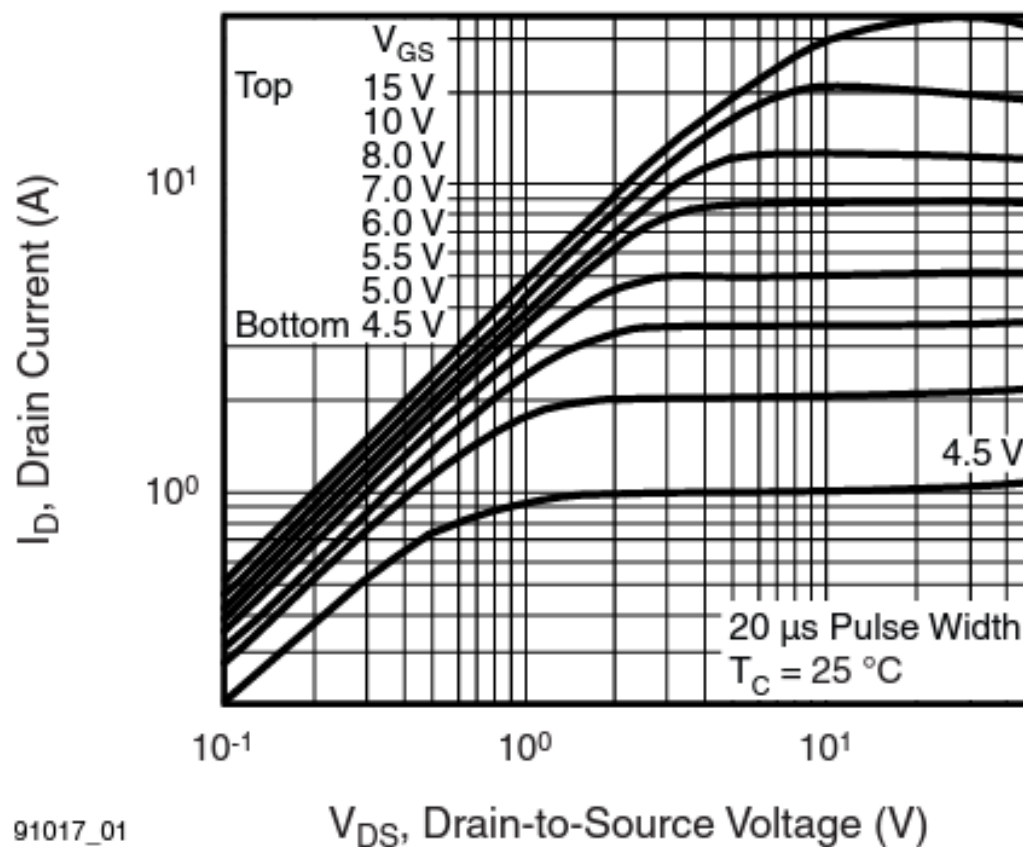


## Regions of operations of MOSFET

Operation Mode	Type	Condition
Cut-Off	NMOS	$V_{GS} < V_{TH}$
	PMOS	$ V_{GS}  <  V_{TH} $
Linear	NMOS	$V_{GS} \geq V_{TH}$ $V_{DS} \leq V_{GS} - V_{TH}$
	PMOS	$ V_{GS}  \geq  V_{TH} $ $ V_{DS}  \leq  V_{GS}  -  V_{TH} $
Saturation	NMOS	$V_{GS} \geq V_{TH}$ $V_{DS} \geq V_{GS} - V_{TH}$
	PMOS	$ V_{GS}  \geq  V_{TH} $ $ V_{DS}  \geq  V_{GS}  -  V_{TH} $



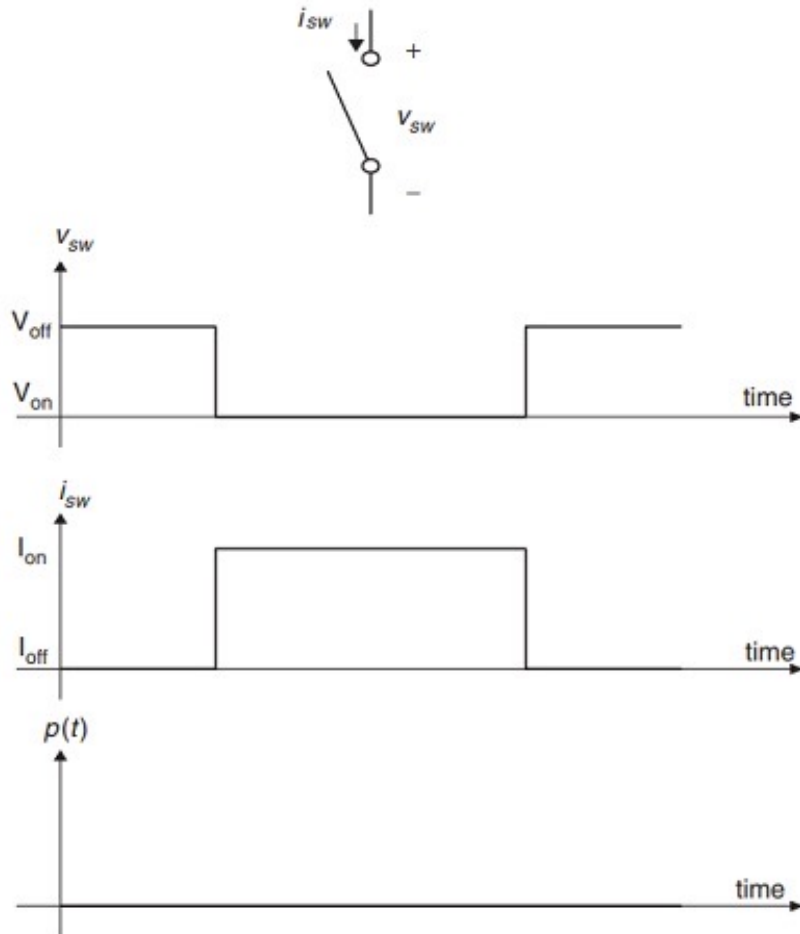




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**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$**

# Ideal Switch vs. Practical Switch



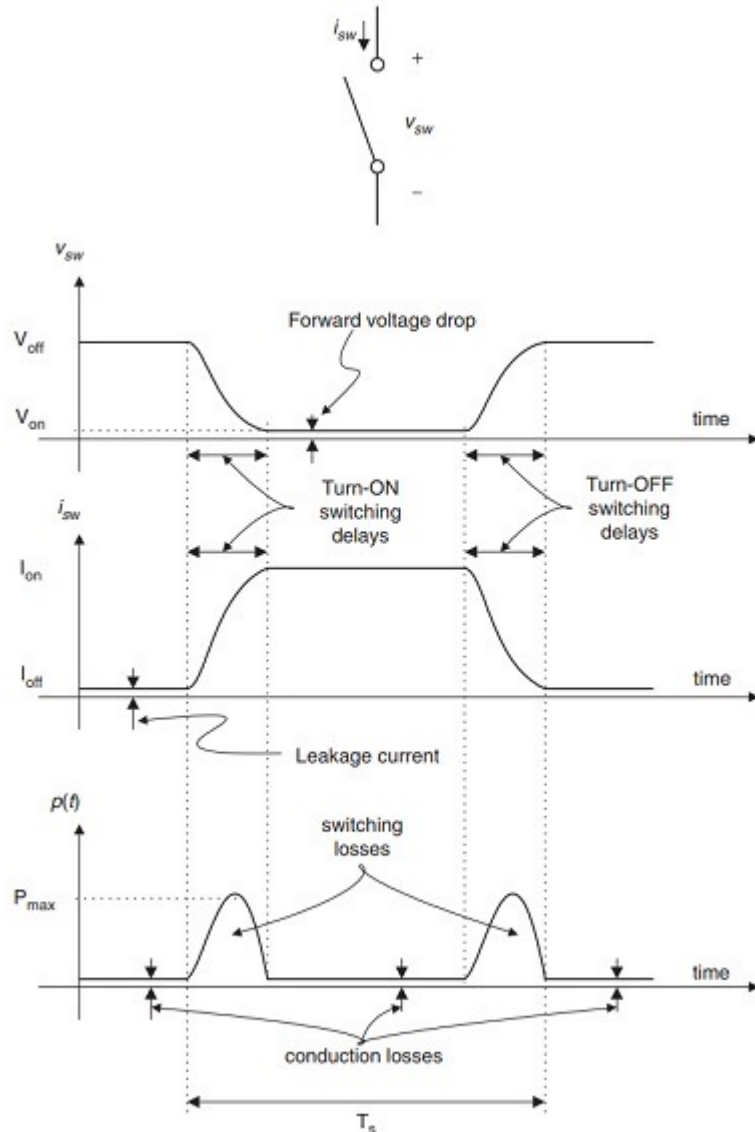
ON state:

- No limit on the current it can carry.
- Zero voltage drop.

OFF state:

- No limit on the blocking voltage.
- OFF state resistance should be infinite.

The operating speed of the device has no limits.



## Power handling capabilities

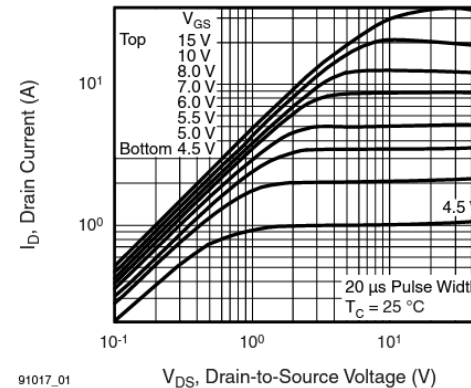


Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$

## Finite on-state resistance

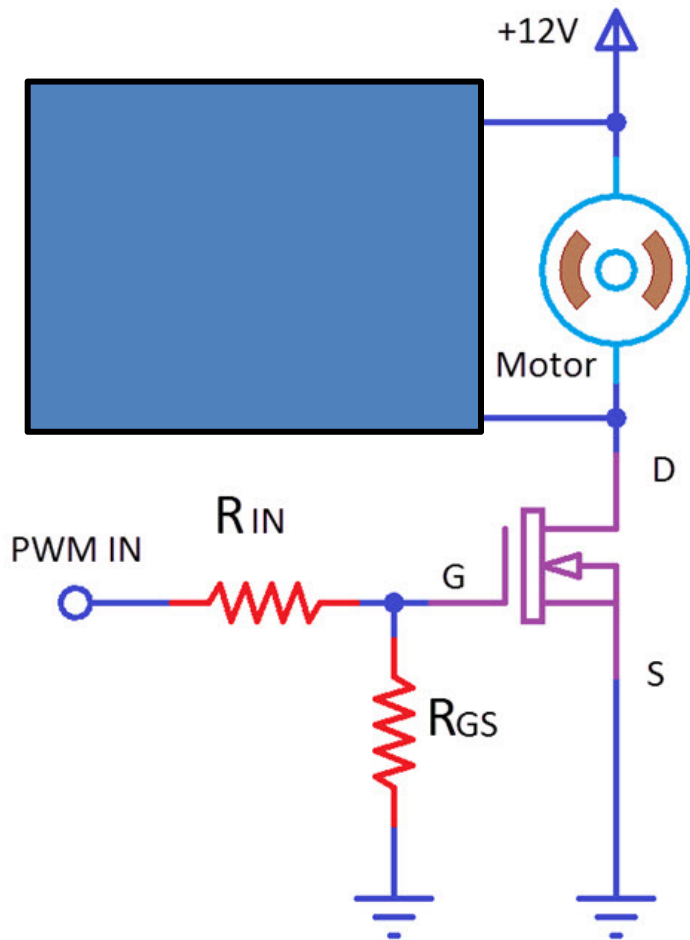
$R_{DS(on)} (\Omega)$	$V_{GS} = 10\text{ V}$	0.27
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Finite off-state resistance, which results in a reverse leakage current and 100V max  $V_{DS}$ .

## Limited speed of operation

Power losses during the transition of states.

## Back EMF and flyback diode



Look at those spikes! And there is a limited on  $V_{ds}$

